



Parameter	Symbol	Conditions
Conductivity	σ	Temperature dependent
Permittivity	ϵ	Frequency dependent
Viscosity	η	Temperature dependent
Density	ρ	Temperature dependent
Diffusion coefficient	D	Temperature dependent
Electron mobility	μ_e	Temperature dependent
Hole mobility	μ_h	Temperature dependent
Recombination coefficient	k_r	Temperature dependent
Generation rate	G	Light intensity dependent
Carrier lifetime	τ	Temperature dependent
Bandgap energy	E_g	Material property
Effective electron mass	m_e^*	Material property
Effective hole mass	m_h^*	Material property
Thermal voltage	V_T	Temperature dependent
Equilibrium constant	K	Temperature dependent
Reaction rate constant	k	Temperature dependent
Pre-exponential factor	A	Material property
Activation energy	E_a	Material property
Forward bias voltage	V_F	Applied voltage
Reverse bias voltage	V_R	Applied voltage
Open-circuit voltage	V_{oc}	Device property
Short-circuit current	I_{sc}	Device property
Maximum power point	P_{max}	Device property
Fill factor	FF	Device property
Efficiency	η	Device property
Quantum yield	Φ	Device property
Incident photon flux	Φ_{ph}	Light intensity
Incident power density	P_{inc}	Light intensity
Incident wavelength	λ	Light property
Incident angle	θ	Light property
Incident polarization	ϵ	Light property
Incident medium	n_i	Material property
Incident refractive index	n_i	Material property
Incident permittivity	ϵ_i	Material property
Incident permeability	μ_i	Material property
Incident conductivity	σ_i	Material property
Incident resistivity	ρ_i	Material property
Incident viscosity	η_i	Material property
Incident density	ρ_i	Material property
Incident diffusion coefficient	D_i	Material property
Incident electron mobility	$\mu_{e,i}$	Material property
Incident hole mobility	$\mu_{h,i}$	Material property
Incident recombination coefficient	$k_{r,i}$	Material property
Incident generation rate	G_i	Material property
Incident carrier lifetime	τ_i	Material property
Incident bandgap energy	$E_{g,i}$	Material property
Incident effective electron mass	$m_{e,i}^*$	Material property
Incident effective hole mass	$m_{h,i}^*$	Material property
Incident thermal voltage	$V_{T,i}$	Material property
Incident equilibrium constant	K_i	Material property
Incident reaction rate constant	k_i	Material property
Incident pre-exponential factor	A_i	Material property
Incident activation energy	$E_{a,i}$	Material property
Incident forward bias voltage	$V_{F,i}$	Material property
Incident reverse bias voltage	$V_{R,i}$	Material property
Incident open-circuit voltage	$V_{oc,i}$	Material property
Incident short-circuit current	$I_{sc,i}$	Material property
Incident maximum power point	$P_{max,i}$	Material property
Incident fill factor	FF_i	Material property
Incident efficiency	η_i	Material property
Incident quantum yield	Φ_i	Material property
Incident incident photon flux	$\Phi_{ph,i}$	Material property
Incident incident power density	$P_{inc,i}$	Material property
Incident incident wavelength	λ_i	Material property
Incident incident angle	θ_i	Material property
Incident incident polarization	ϵ_i	Material property
Incident incident medium	$n_{i,i}$	Material property
Incident incident refractive index	$n_{i,i}$	Material property
Incident incident permittivity	$\epsilon_{i,i}$	Material property
Incident incident permeability	$\mu_{i,i}$	Material property
Incident incident conductivity	$\sigma_{i,i}$	Material property
Incident incident resistivity	$\rho_{i,i}$	Material property
Incident incident viscosity	$\eta_{i,i}$	Material property
Incident incident density	$\rho_{i,i}$	Material property
Incident incident diffusion coefficient	$D_{i,i}$	Material property
Incident incident electron mobility	$\mu_{e,i,i}$	Material property
Incident incident hole mobility	$\mu_{h,i,i}$	Material property
Incident incident recombination coefficient	$k_{r,i,i}$	Material property
Incident incident generation rate	$G_{i,i}$	Material property
Incident incident carrier lifetime	$\tau_{i,i}$	Material property
Incident incident bandgap energy	$E_{g,i,i}$	Material property
Incident incident effective electron mass	$m_{e,i,i}^*$	Material property
Incident incident effective hole mass	$m_{h,i,i}^*$	Material property
Incident incident thermal voltage	$V_{T,i,i}$	Material property
Incident incident equilibrium constant	$K_{i,i}$	Material property
Incident incident reaction rate constant	$k_{i,i}$	Material property
Incident incident pre-exponential factor	$A_{i,i}$	Material property
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Incident incident maximum power point	$P_{max,i,i}$	Material property
Incident incident fill factor	$FF_{i,i}$	Material property
Incident incident efficiency	$\eta_{i,i}$	Material property
Incident incident quantum yield	$\Phi_{i,i}$	Material property
Incident incident incident photon flux	$\Phi_{ph,i,i}$	Material property
Incident incident incident power density	$P_{inc,i,i}$	Material property
Incident incident incident wavelength	$\lambda_{i,i}$	Material property
Incident incident incident angle	$\theta_{i,i}$	Material property
Incident incident incident polarization	$\epsilon_{i,i}$	Material property
Incident incident incident medium	$n_{i,i,i}$	Material property
Incident incident incident refractive index	$n_{i,i,i}$	Material property
Incident incident incident permittivity	$\epsilon_{i,i,i}$	Material property
Incident incident incident permeability	$\mu_{i,i,i}$	Material property
Incident incident incident conductivity	$\sigma_{i,i,i}$	Material property
Incident incident incident resistivity	$\rho_{$	

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Typical Performance Characteristics

Figure1. Output Characteristics

Figure2. Transfer Characteristics

Figure3. Capacitance Characteristics

Figure4. Gate Charge

Figure5. Drain-Source on Resistance

Figure6. Drain Current



SOP-8 Package information

SYMBOL	MIN.		
	0.053	0.069	
B	0.004	0.010	
		0.061	
D		0.020	
E			
F			
G	0.050BSC		1.270BSC
H			
J			
K			



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